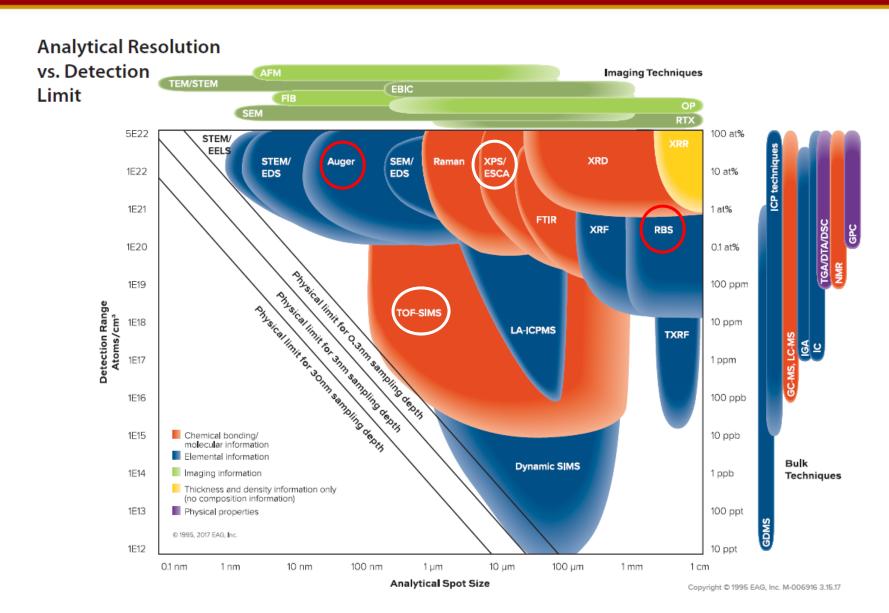
Surface Analytical Techniques (XPS, Auger, SIMS and RBS)

Jerry Hunter, Ph. D.

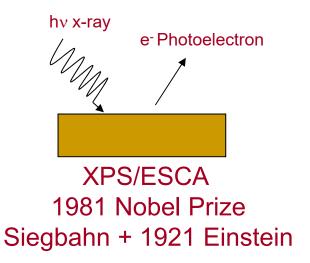
Analytical Methods

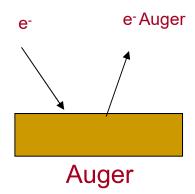




Electron Spectroscopy







XPS Key ideas to take away

- XPS provides detection limits to ~0.1% atomic
- XPS is very surface sensitive (top <10 nm)
- XPS gives chemical bonding information
- XPS is useful for surveys of unknown contamination
- Can combine with ion sputtering to perform compositional depth profiling

X-ray Photoelectron Spectroscopy (XPS)



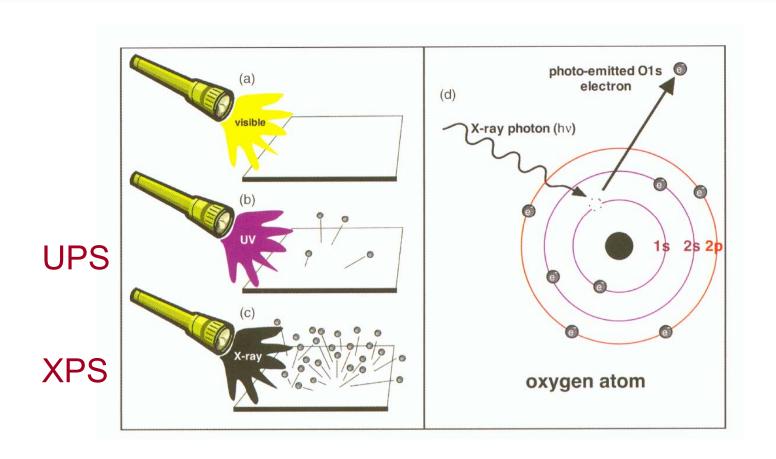
- X-ray beam irradiates a sample surface resulting in the ejection of photoelectrons from the core level of the atoms present in the sample
- Photoelectrons are extracted and filtered with respect to their energy (energy is representative of the elements in the sample)
- Can be combined with sputtering to do depth profiling

X-ray Photoelectron Spectroscopy (XPS)

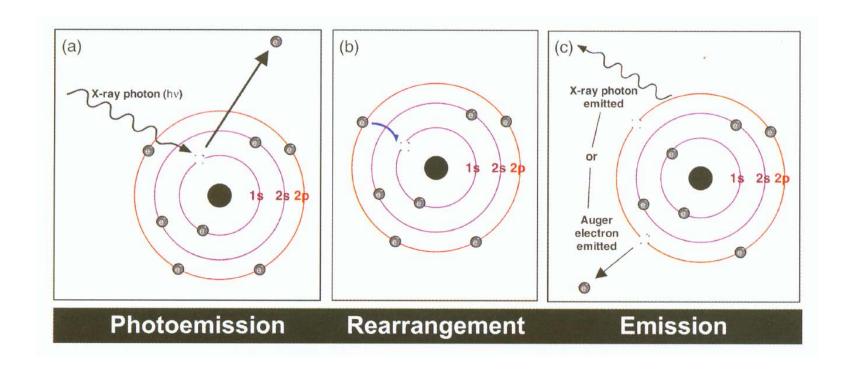


- Signal detected: Photoelectrons from near surface atoms
- Elements detected: Li U, Chemical bonding
- Detection limit: 0.1 1% atomic
- Imaging: Yes
- Lateral Resolution: 9um 2mm

Photoelectric Effect



Photoemission Process



X-ray photoelectron spectroscopy, XPS (a.k.a. Electron Spectroscopy for Chemical Analysis, ESCA)



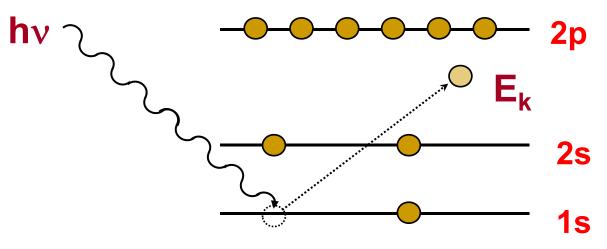
Photoelectric effect:

Photon of energy, $h\nu$, bombards a material and is absorbed by an electron with binding energy E_b which then is ejected into the vacuum with kinetic energy,

$$E_k = h_V - E_b - \phi$$

where,

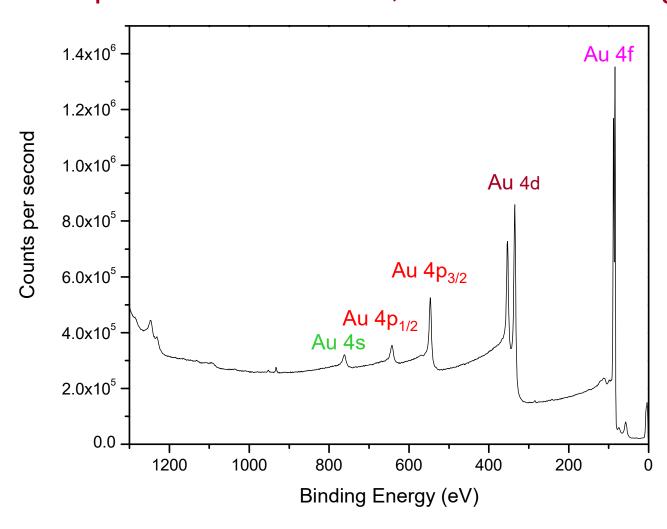
 ϕ = work function to remove the electron from the surface



XPS Survey Spectra of Gold foil



note peaks have discrete, well defined energies



XPS Strengths and Limitations



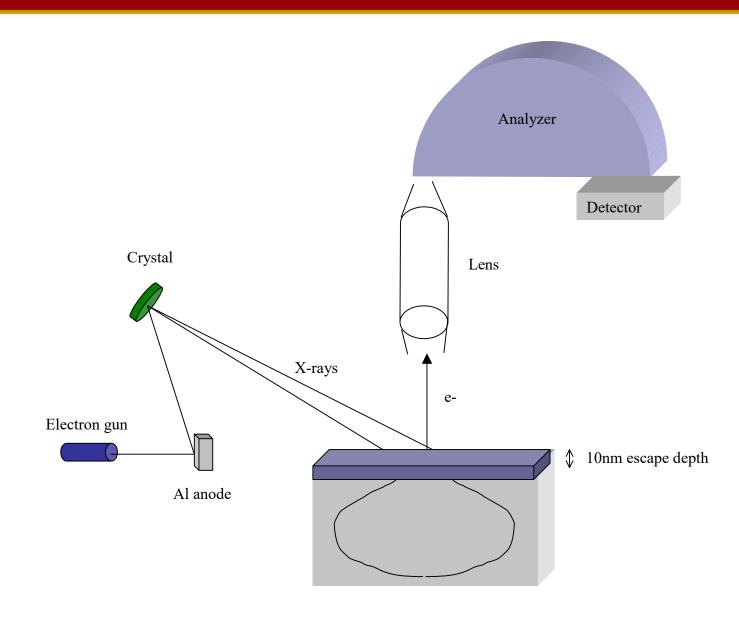
Strengths

- Can detect Li-U
- Surface sensitive (1-10nm sampling depth)
- Sensitive to differences in chemical environment
- Quantitative without standards
- Works well on insulating materials

Limitations

- Poor lateral resolution (~10 μm)
- Surface sensitive
- Detection limit ~0.1% atomic
- Cannot detect H

The XPS Experiment



Types of XPS data

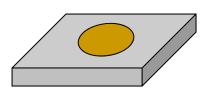


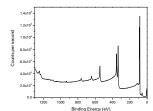
- Spectra
 - Survey a wide energy scan to see all elemental lines
 - High resolution scans narrow energy scans to look at chemical bonding for specific elemental lines
- Depth profiles
 - Sputter depth profiles for composition vs. depth up to a few μm
- XPS maps
 - Elemental or bonding information images with ~10 μm resolution

Modes of data acquisition

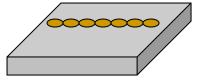
Point mode (spectra)

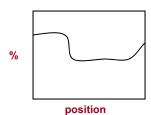
Most common analysis approach;
variable analysis size



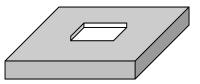


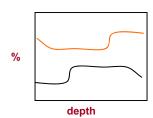
Line scan (1-D surface scan)



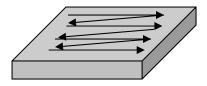


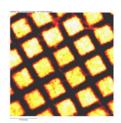
Depth Profile





Mapping (2-D surface image)

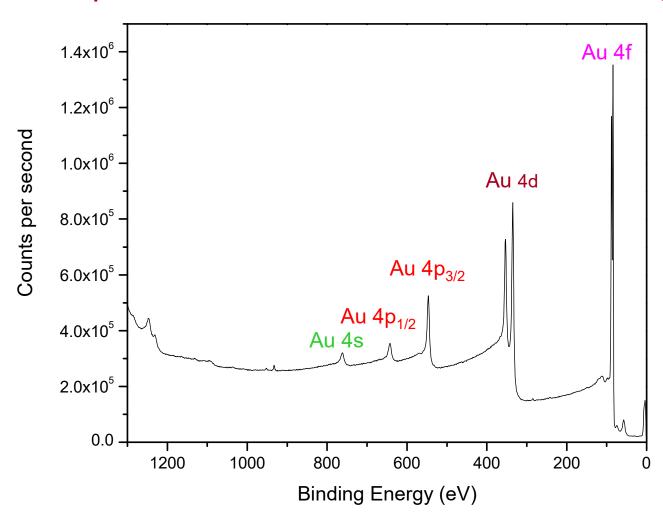




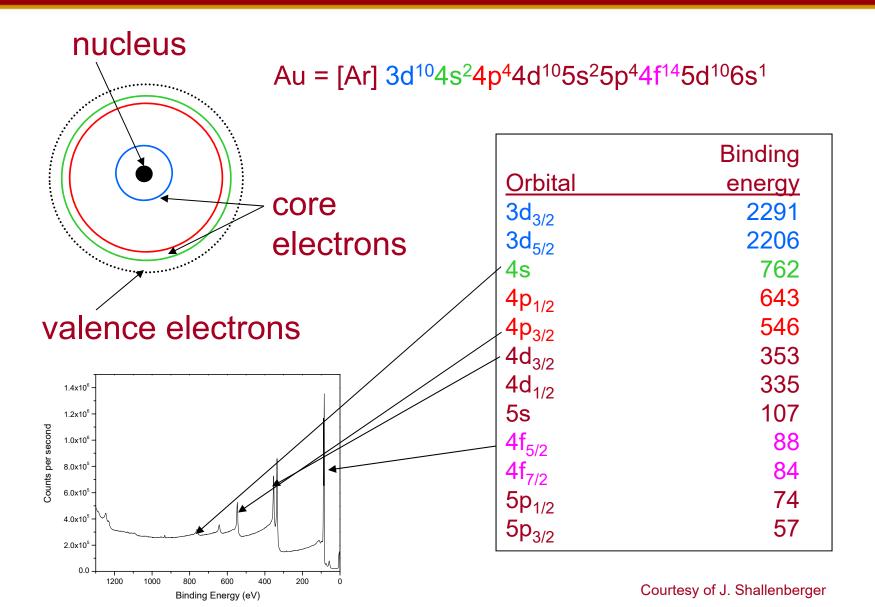




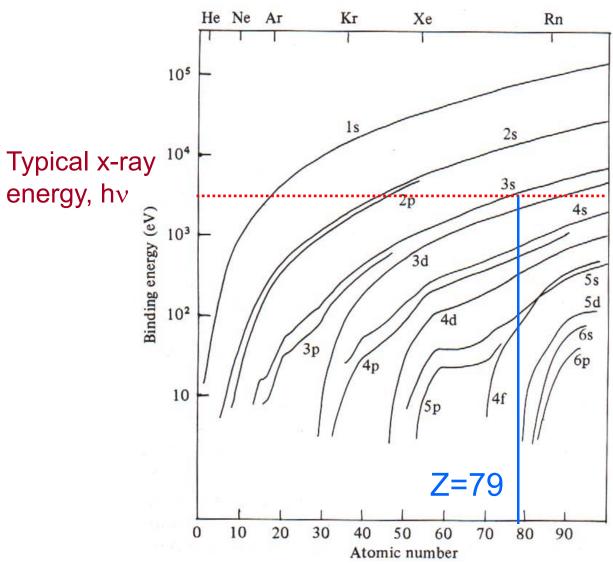
note peaks have discrete, well defined energies



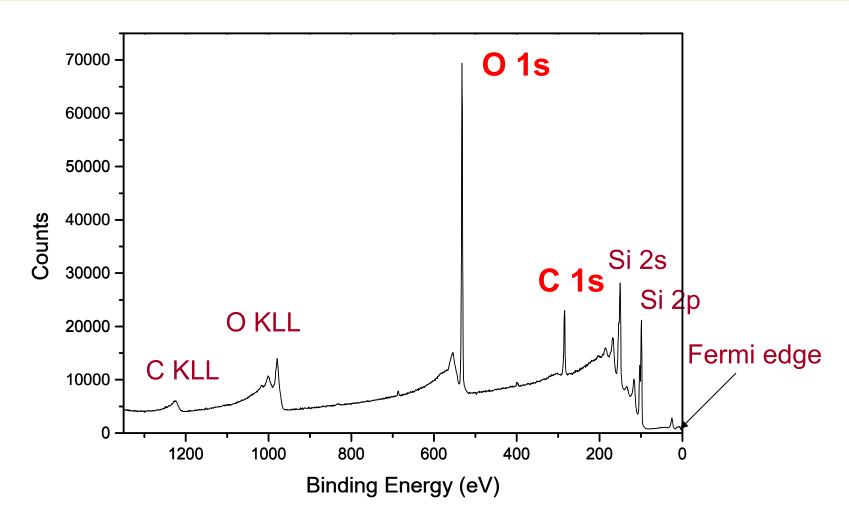
Gold electronic structure



XPS capable of identifying Li-U



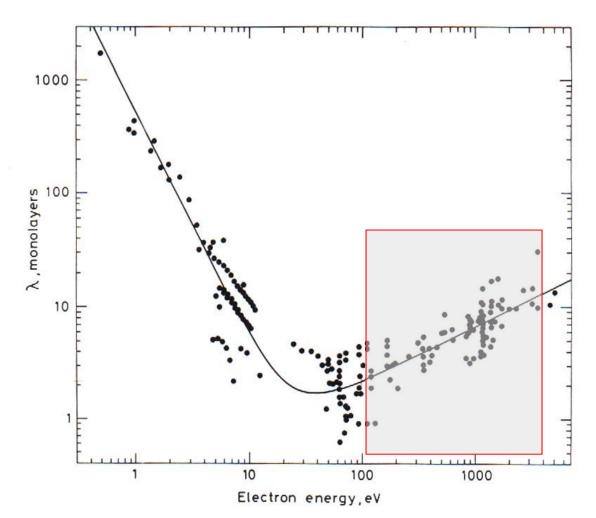
Photoelectron spectrum of silicon wafer



Always see C and O, due to high surface sensitivity

Surface Sensitivity

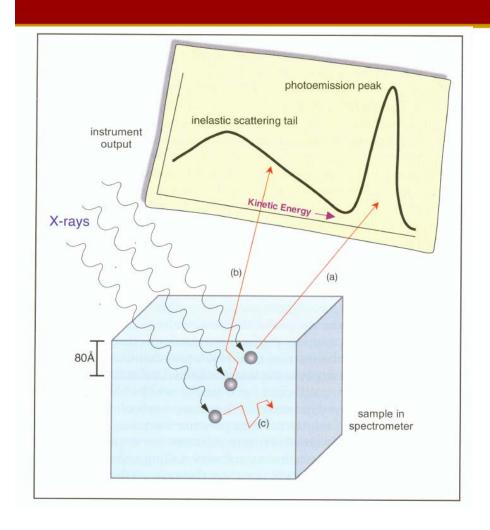




- XPS is surface sensitive because an electron with kinetic energy < 1,500 eV will NOT travel very far through a solid

from Briggs and Seah, Practical Surface Analysis 2nd Edition John Wiley & Sons (Chichester) 1990, p. 207.

Surface Sensitivity



- X-rays penetrate deeply into sample causing electron emission
- Only electrons emitted near the surface that have escaped with no energy loss will contribute to the photoemission peak
- Some electrons have experienced inelastic collisions prior to escaping the sample surface and will present as a background in the spectrum
- Electrons that are too deep have insufficient energy to escape the surface
- Analytical depth is determined by the distance a photoelectron can travel without the loss of energy

Vickerman

Chemical Shift



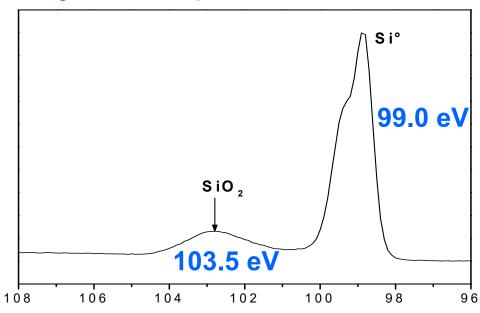
- Binding energy of core electrons can change when the chemical environment changes
- Generally, the binding energies of core levels increase when valence electrons are removed from an atom
- Binding energies of core levels decrease when valence electrons are added to an atom

General observations in chemical shifts



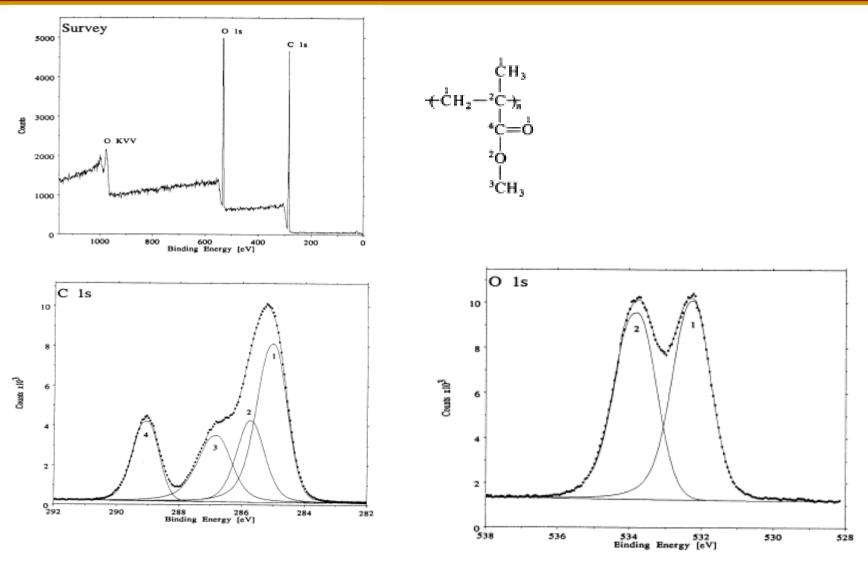
- (1) higher valence oxidation state species has electrons bound with higher energy compared with more reduced state
- (2) In atoms with same formal valence state, BE increases with electronegativity of neighboring atoms

High resolution spectrum



XPS of Poly (methyl methacrylate) PMMA





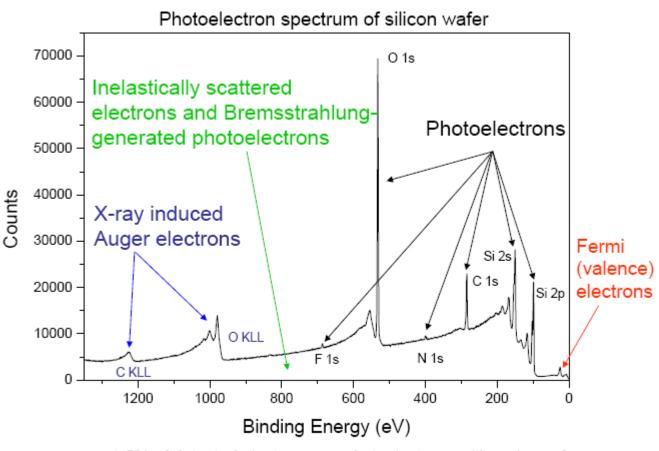
XPS of Polymers Database ed: G. Beamson and D. Briggs



Spectral Features in XPS

XPS Spectral Features

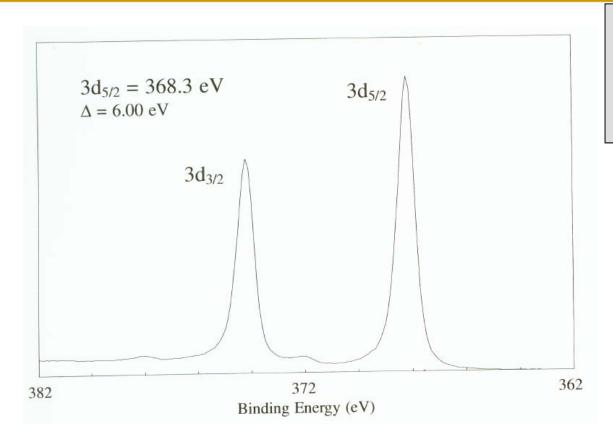




1-5% of detected electrons are photoelectrons with no loss of energy



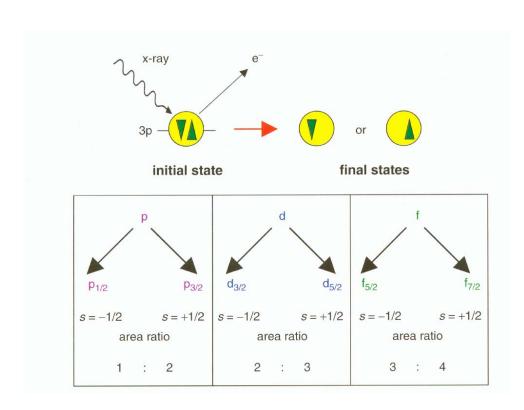




Subshell	<i>j</i> value	Area ratio
S	1/2	-
p	1/2, 3/2	1:2
d	3/2, 5/2	2:3
f	5/2, 7/2	3:4

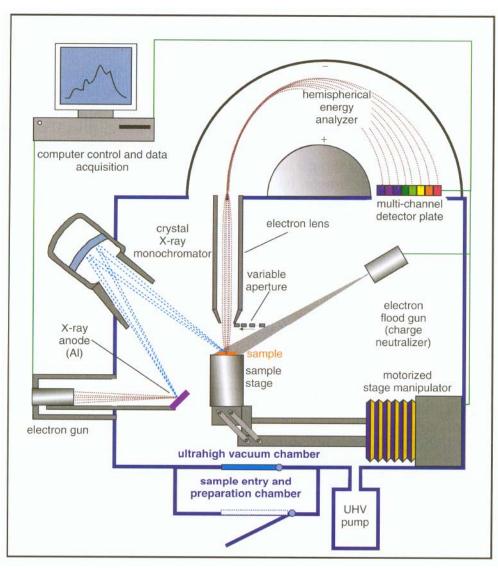
Peak ratios given by: 2j+1

Spin-Orbit Splitting



- After electron emission from a 3p orbital subshell, remaining electron can have either spin-up or spin-down state
- Magnetic interaction between these electrons and the orbital angular momentum leads to spinorbit splitting

XPS instrumentation



XPS Summary



- Elemental sensitivity
 - Range Li U
 - Excellent specificity
 - Detection limits 0.1 1 atomic %
- Spatial resolution
 - Few μm for commercial systems
- Analysis depth
 - Depends on material and photoelectron energy
 - Can sputter depth profile for larger depths

- Quantitative
 - Homogeneous samples easier
 - Need reliable sensitivity factors
- Chemical information
 - Chemical shift can give bonding information

The Auger Experiment

Auger is essentially an XPS (electron energy analyzer) hooked up to an SEM Analyzer Lens Auger e-Detector 10nm escape depth Possible to perform XPS on an Auger simply by adding an X-ray source

Auger Process



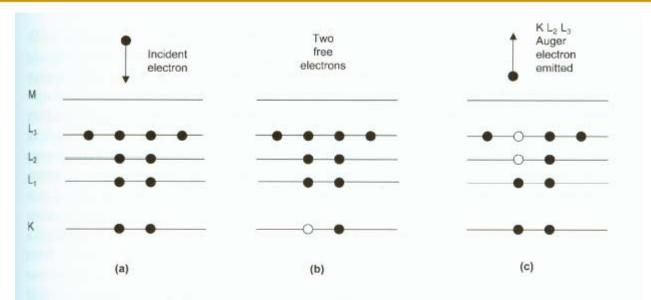


Figure 1. Illustration of the KL_2L_3 Auger process: (a) atom showing electrons present in filled K and L levels before an electron is removed from the K level, (b) after removal of an electron from the K level and (c) following the Auger process where a KL_2L_3 Auger electron is emitted. In (c) one L level electron fills the K vacancy and the other L level electron is ejected due to the energy available on filling the K level.

Auger Summary



- Elemental sensitivity
 - Range Li U
 - Excellent specificity
 - Sensitivity factor variation is ~100
 - Detection limits 0.1 1 atomic %
- Spatial resolution
 - 10-20 nm for commercial systems
- Analysis depth
 - Depends on material and Auger electron energy
 - Can sputter depth profile for larger depths

- Quantitative
 - Not as straightforward as XPS
 - Need reliable sensitivity factors
- Chemical information
 - Chemical shift in some cases
- Beam damage
 - More significant problem vs. XPS
- Sample charging is an issue

Auger vs. XPS

- XPS better able to analyze insulating materials
- Spot size is orders of magnitude smaller with AES allowing chemical analysis of nm size spots
- Narrow XPS peaks allow chemical analysis
- High resolution elemental maps possible with AES
- Both capable of elemental depth profiling

Auger and XPS



Similar

- Surface sensitivity (all of the discussion about IMFP, mean escape depth, etc. holds for the Auger electrons
- Kinetic energies are typically 100ev 2kV
- Cost of instrument (\$500K \$1M)
- Typically same type of analyzer
- Detection limits
- Elements detected (Li-U)
- Depth profiling by sputtering

Different

- Excitation source is electrons
- Multi-electron process
- Much higher lateral resolution (10nm vs. 10,000 nm)
- Much higher background
- More typically used for elemental information
- Higher likelihood of beam damage from e-beam

Electron Spectroscopy = Surface Analysis

- Identification of elements present at the surface – qualitative analysis
- Quantitative analysis of elements at the surface
- Chemical bonding information
- Distribution of elements across the surface
 - elemental image or map
- Change in composition with depth depth profile

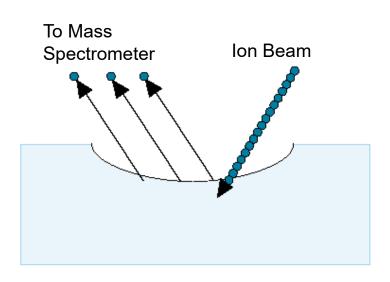
Electron Spectroscopy Key ideas to take away

- Electron spectroscopy provides detection limits to ~0.1% atomic
- Both XPS and Auger are very surface sensitive (top <10 nm)
- Auger has much better (~10nm) lateral resolution than XPS (1 – 10 um)
- XPS gives chemical bonding information
- Auger and XPS are useful for surveys of unknown contamination
- When combined with ion sputtering can perform compositional depth profiling

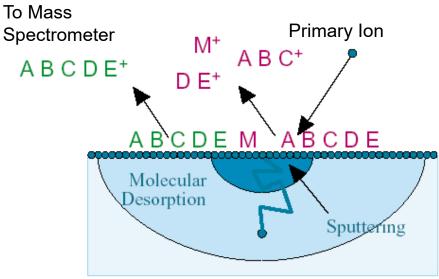
Dynamic and Static Modes of Operation



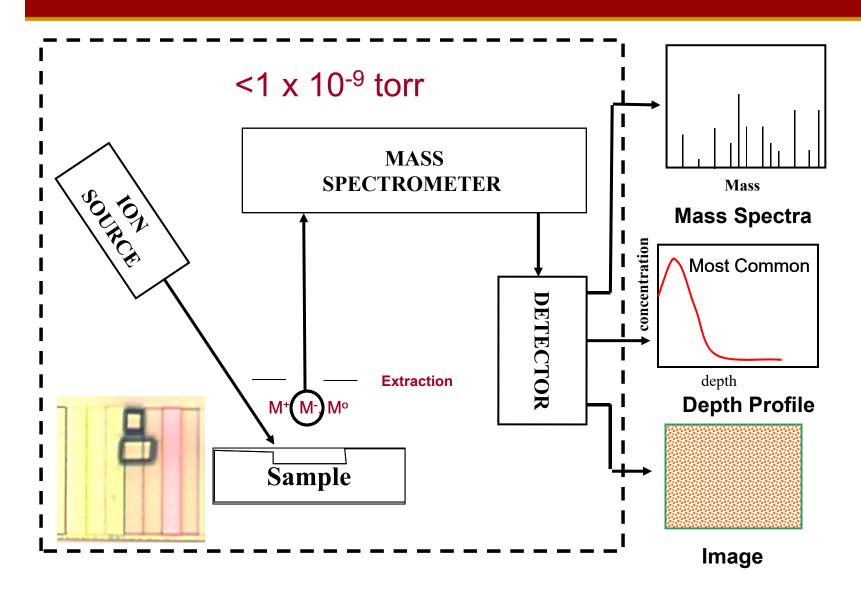
Dynamic SIMS



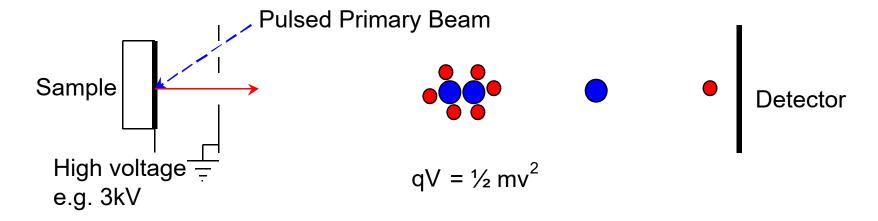
Static SIMS



SIMS Technique



Time-of-Flight SIMS: Basic Principles



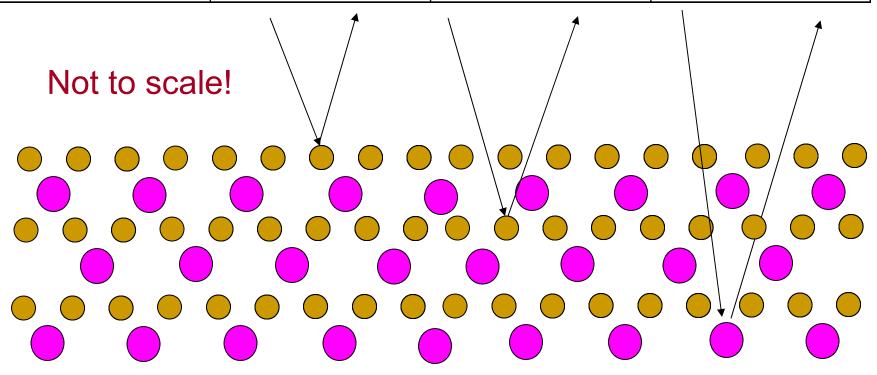
Flight time of each ion is recorded: $t = k(m)_{2}^{1/2}$

Convert time axis to mass by rearrangement: $m = at^2 + b$

- Quasi-parallel detection of entire mass spectrum
- Unlimited mass range

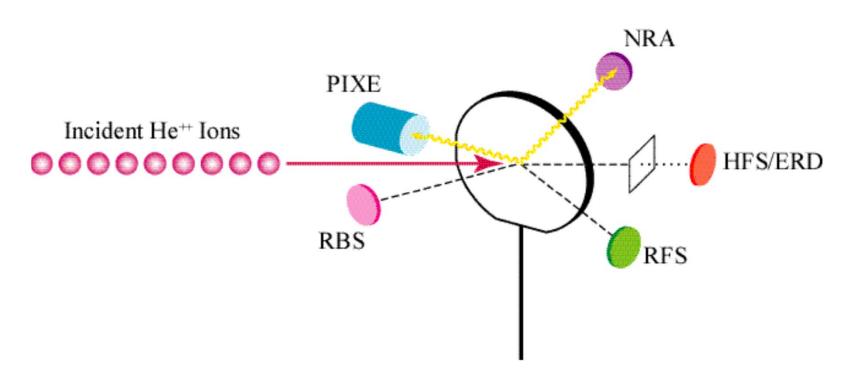
Scattering Methods

Technique	ISS/LEIS	MEIS	RBS
Ions	1-2kV He ⁺ or Ne ⁺	50-500kV H ⁺ or He ⁺	1-3MeV H ⁺ or He ⁺
Depth resolution	Top surface	0.3-1nm	5-50nm
Maximum depth	Surface	Surface-50nm	2-20μm



MeV Ion Beam Processes

Techniques

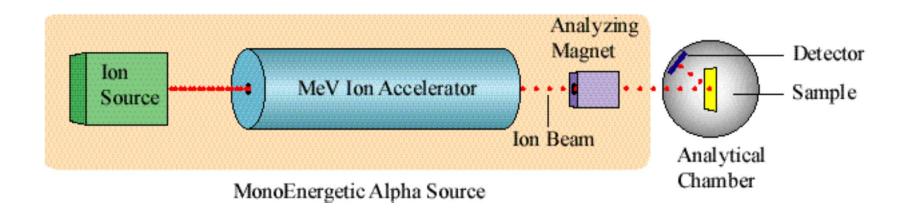


RBS Accelerator System



Instrument Configuration

- MeV ions from an electrostatic accelerator are focused on a sample in a vacuum chamber for analysis.
- Typically, 2 MeV He⁺⁺ ions are used.



Analysis of Tungsten Silicide

Comparison of Three WSi_x Films

